

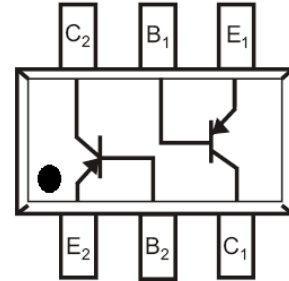


Features

- Epitaxial planar die construction
- Ideal for low power amplification and switching
- Ultra-small surface mount package

Mechanical Data

- Case: SOT-563
- Molding compound: UL flammability classification rating 94V-0
- Terminal s: Tin-plated; solderability per MIL-STD-202, Method 208



SOT-563

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CB0}	-40	V
Collector-Emitter Breakdown Voltage	V _{CEO}	-40	V
Emitter-Base Breakdown Voltage	V _{EBO}	-5	V
Collector Current (Continuous)	I _C	-0.2	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (Collector) *1	P _C	150	mW
Thermal Resistance (Junction-to-Ambient) *1	R _{θJA}	833	°C/W
Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

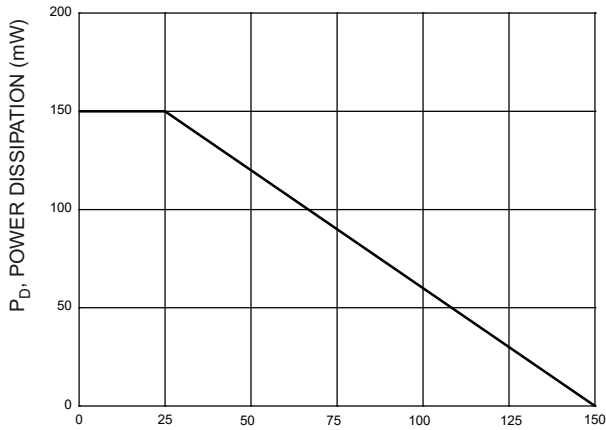
Note 1: Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

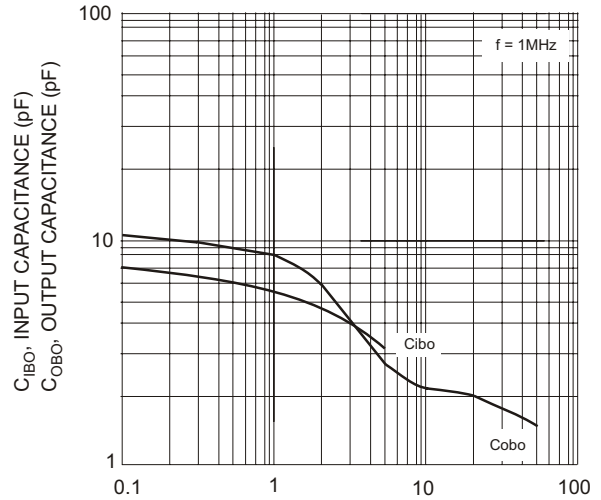
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CEX}	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$	-	-	-50	nA
Base Cut-off Current	I_{BL}	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$	-	-	-50	nA
DC Current Gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -0.1\text{mA}$	60	-	-	-
		$V_{CE} = -1\text{V}, I_C = -1\text{mA}$	80	-	-	-
		$V_{CE} = -1\text{V}, I_C = -10\text{mA}$	100	-	300	-
		$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	60	-	-	-
		$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	30	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$	-	-	-0.25	V
		$I_C = -50\text{mA}, I_B = -5\text{mA}$	-	-	-0.4	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$	-0.65	-	-0.85	V
		$I_C = -50\text{mA}, I_B = -5\text{mA}$	-	-	-0.95	V
Output Capacitance	C_{OBO}	$V_{CB} = -5\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$	-	-	4.5	pF
Input Capacitance	C_{IBO}	$I_C = 0, V_{EB} = -0.5\text{V}, f = 1\text{MHz}$	-	-	10	pF
Transition Frequency	f_T	$I_C = -1\text{mA}, V_{CE} = -10\text{V}$ $f = 1\text{KHz}$	250	-	-	MHZ
Noise Figure	NF	$I_C = -0.1\text{mA}, V_{CE} = -20\text{V}$ $f = 100\text{MHz}$	-	-	4	dB
Delay Time	t_d	$V_{CC} = -3\text{V}, V_{BE(off)} = 0.5\text{V}$	-	-	35	ns
Rise Time	t_r	$I_C = -10\text{mA}, I_{B1} = -1\text{mA}$	-	-	35	ns
Storage Time	t_s	$V_{CC} = -3\text{V}, I_C = -10\text{mA}$	-	-	225	ns
Fall Time	t_f	$I_{B1} = I_{B2} = -1\text{mA}$	-	-	75	ns

Ratings and Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)



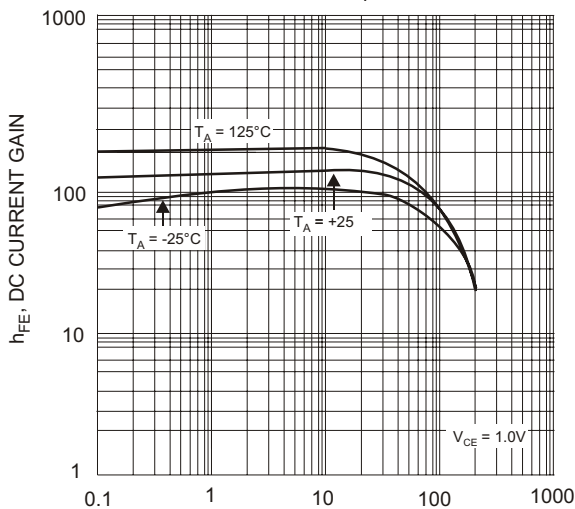
T_A , AMBIENT TEMPERATURE ($^\circ\text{C}$)

Fig. 1, Max Power Dissipation vs Ambient Temperature



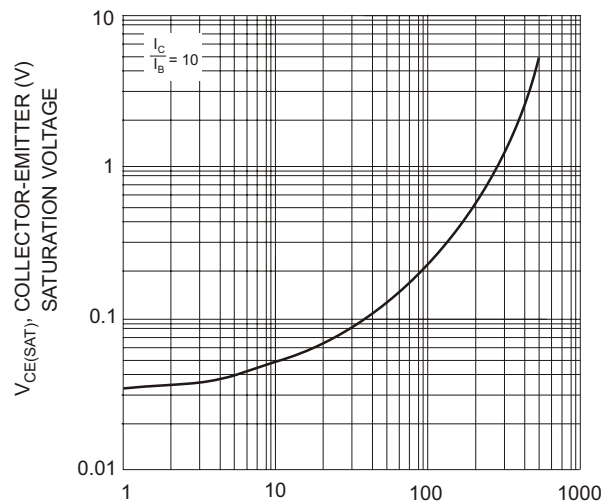
V_{CB} , COLLECTOR-BASE VOLTAGE (V)

Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



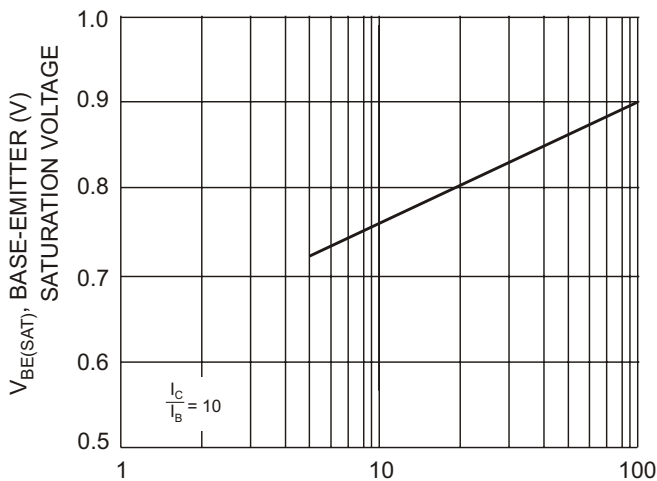
I_C , COLLECTOR CURRENT (mA)

Fig. 3, Typical DC Current Gain vs Collector Current



I_C , COLLECTOR CURRENT (mA)

Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

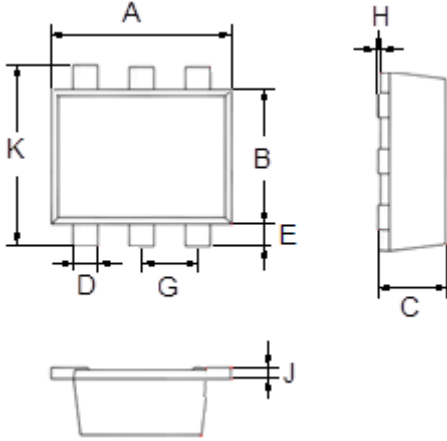


I_C , COLLECTOR CURRENT (mA)

Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current



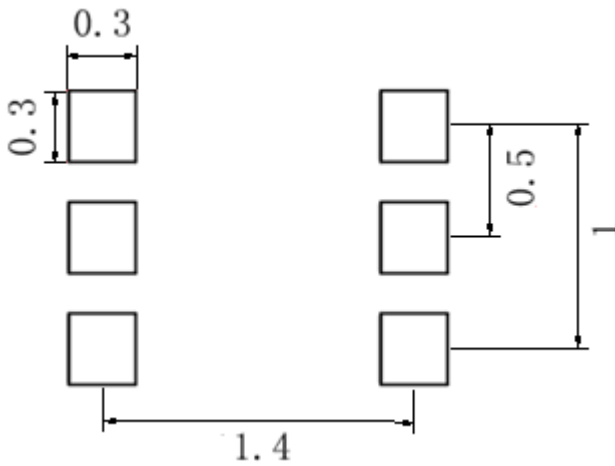
Package Outline Dimensions (Unit: mm)



SOT-563		
Dimension	Min.	
A	1.500	1.700
B	1.100	1.300
C	0.525	0.600
D	0.170	0.270
E	0.100	0.300
G	0.450	0.550
H	0.000	0.050
J	0.090	0.160
K	1.500	1.700

Package Outline Dimensions (Unit: mm)

SOT-563



Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMDT3906V	SOT-563	3000pcs / Tape & Reel	KAR